

# FDS6673AZ

## 30 Volt P-Channel PowerTrench® MOSFET

### Features

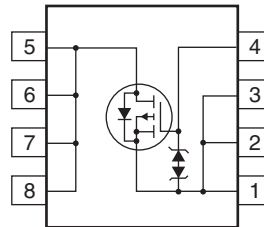
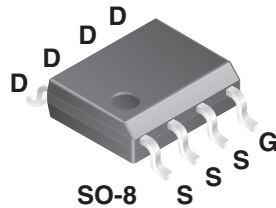
- -14.5 A, -30 V.  $R_{DS(ON)} = 7.2 \text{ m}\Omega @ V_{GS} = -10 \text{ V}$   
 $R_{DS(ON)} = 11 \text{ m}\Omega @ V_{GS} = -4.5 \text{ V}$
- Extended  $V_{GSS}$  range (-25V) for battery applications
- ESD protection diode (note 3)
- High performance trench technology for extremely low  $R_{DS(ON)}$
- High power and current handling capability

### General Description

This P-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers, and battery chargers.

These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable  $R_{DS(ON)}$  specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.



### Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units	
$V_{DSS}$	Drain-Source Voltage	-30	V	
$V_{GSS}$	Gate-Source Voltage	$\pm 25$	V	
$I_D$	Drain Current	- Continuous	(Note 1a) -14.5	A
		- Pulsed	-50	
$P_D$	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1.2	
		(Note 1c)	1.0	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +175	$^\circ\text{C}$	
<b>Thermal Characteristics</b>				
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a) 50	$^\circ\text{C/W}$	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1) 25	$^\circ\text{C/W}$	

### Package Marking and Ordering Information

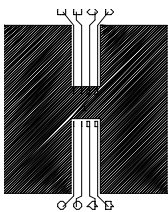
Device Marking	Device	Reel Size	Tape width	Quantity
FDS6673AZ	FDS6673AZ	13"	12mm	2500 units

**Electrical Characteristics**  $T_A = 25^\circ\text{C}$  unless otherwise noted

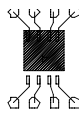
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		-25		$\text{mV}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
$I_{GSS}$	Gate-Body Leakage	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$			$\pm 10$	$\mu\text{A}$
<b>On Characteristics (Note 2)</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-1	-1.6	-3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		5.8		$\text{mV}/^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{ V}, I_D = -14.5\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -12\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -14.5\text{ A}, T_J = 125^\circ\text{C}$		6.0 8.8 7.8	7.2 11 10.4	$\text{m}\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = -5\text{ V}, I_D = -14.5\text{ A}$		50		S
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$		4480		pF
$C_{oss}$	Output Capacitance			1190		pF
$C_{rss}$	Reverse Transfer Capacitance			615		pF
$R_G$	Gate Resistance	$V_{GS} = 15\text{ mV}, f = 1.0\text{ MHz}$		3.8		
<b>Switching Characteristics (Note 2)</b>						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -15\text{ V}, I_D = -1\text{ A}, V_{GS} = -10\text{ V}, R_{GEN} = 6\ \Omega$		22	35	ns
$t_r$	Turn-On Rise Time			8	16	ns
$t_{d(off)}$	Turn-Off Delay Time			134	214	ns
$t_f$	Turn-Off Fall Time			79	126	ns
$Q_g$	Total Gate Charge	$V_{DS} = -15\text{ V}, I_D = -14.5\text{ A}, V_{GS} = -10\text{ V}$		84	118	nC
$Q_{gs}$	Gate-Source Charge			12		nC
$Q_{gd}$	Gate-Drain Charge			19		nC
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain-Source Diode Forward Current				-2.1	A
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -2.1\text{ A}$ (Note 2)		-0.7	-1.2	V
$t_{RR}$	Reverse Recovery Time	$I_F = -14.5\text{ A}, d_i/d_t = 100\text{ A}/\mu\text{s}$ (Note 2)		44		ns
$Q_{RR}$	Reverse Recovery Charge			29		nC

**Notes:**

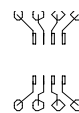
- $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a)  $50^\circ\text{C}/\text{W}$  (10 sec)  $62.5^\circ\text{C}/\text{W}$  steady state when mounted on a  $1\text{ in}^2$  pad of 2 oz copper



b)  $105^\circ\text{C}/\text{W}$  when mounted on a  $.04\text{ in}^2$  pad of 2 oz copper



c)  $125^\circ\text{C}/\text{W}$  when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width <  $300\ \mu\text{s}$ , Duty Cycle < 2.0%
- The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

## Typical Characteristics

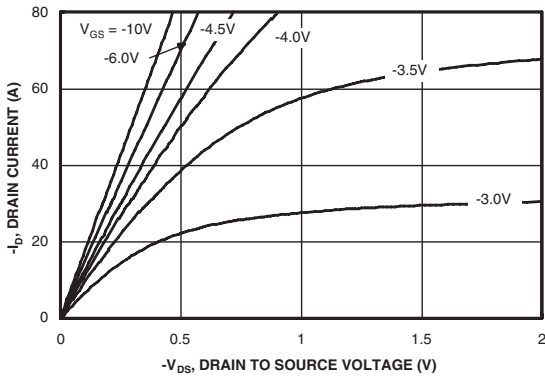


Figure 1. On-Region Characteristics.

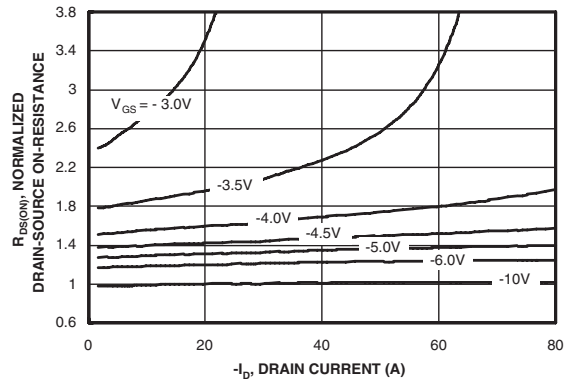


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

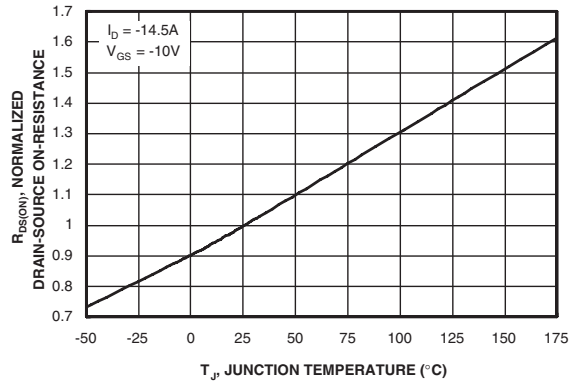


Figure 3. On-Resistance Variation with Temperature.

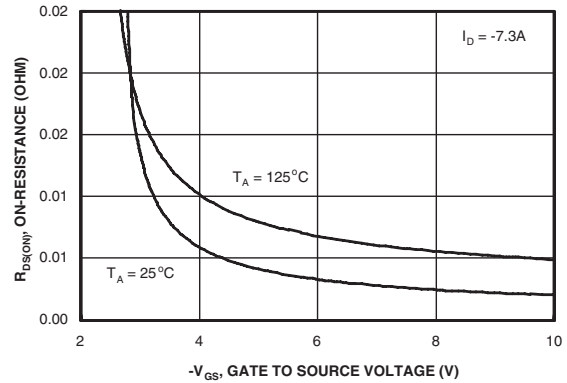


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

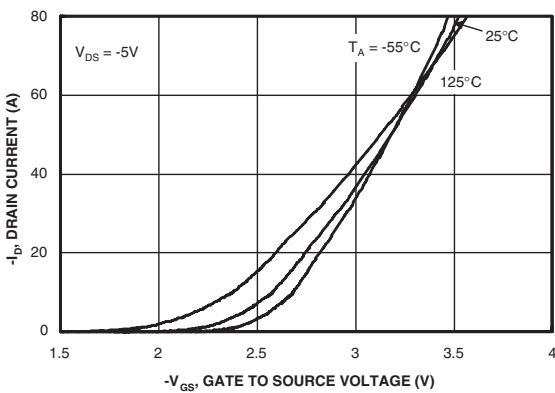


Figure 5. Transfer Characteristics.

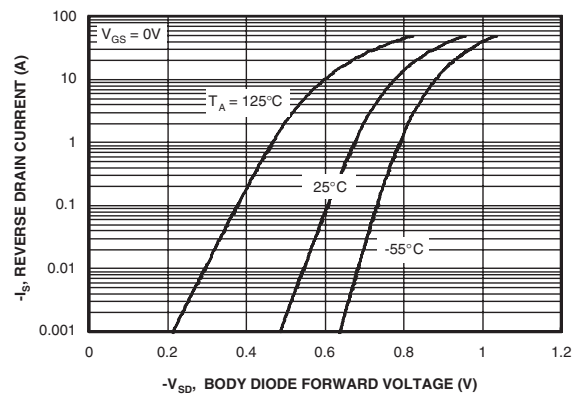


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

## Typical Characteristics

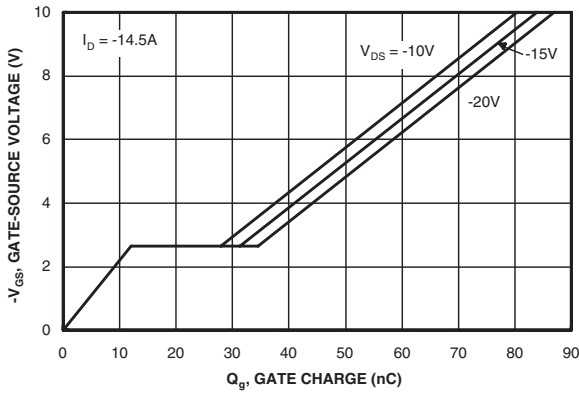


Figure 7. Gate Charge Characteristics.

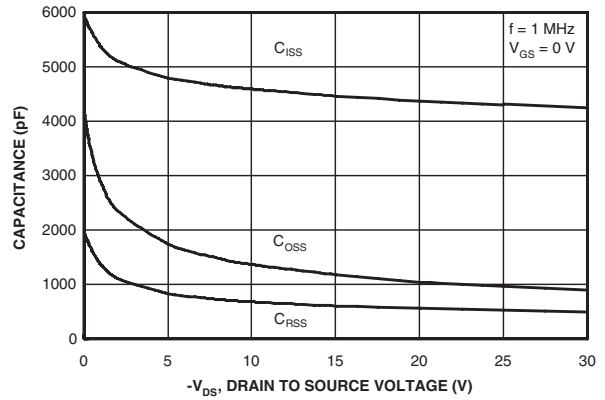


Figure 8. Capacitance Characteristics.

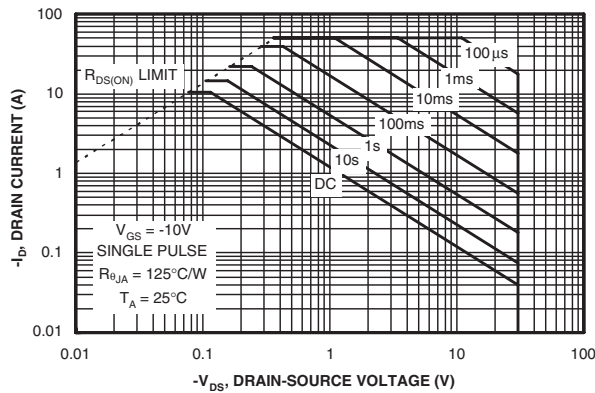


Figure 9. Maximum Safe Operating Area.

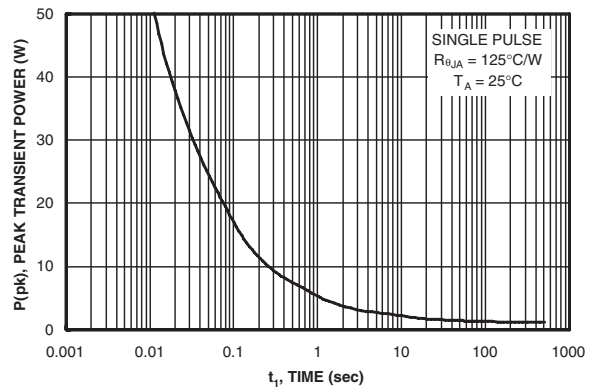


Figure 10. Single Pulse Maximum Power Dissipation.

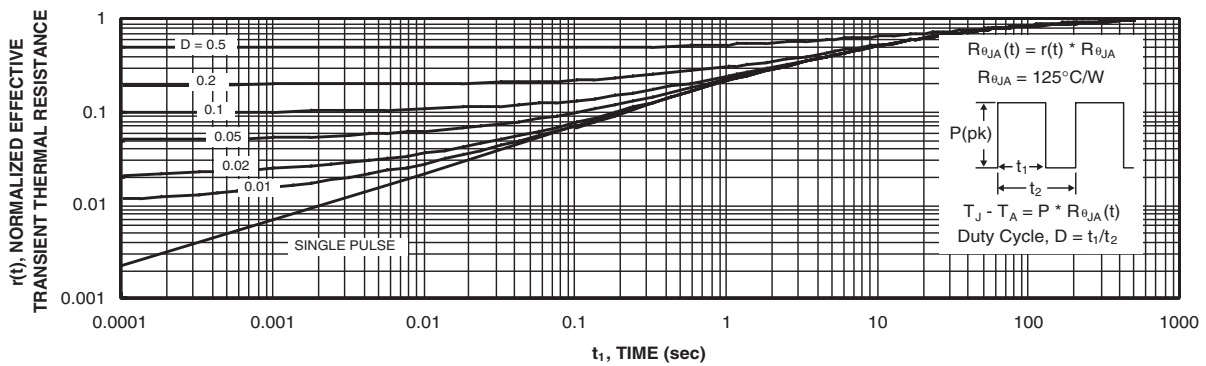


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.  
Transient thermal response will change depending on the circuit board design.

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